# 74AHC1G79; 74AHCT1G79

# Single D-type flip-flop; positive-edge trigger Rev. 05 — 2 July 2007

**Product data sheet** 

#### **General description** 1.

74AHC1G79 and 74AHCT1G79 are high-speed Si-gate CMOS devices. They provide a single positive-edge triggered D-type flip-flop.

Information on the data input is transferred to the Q output on the LOW-to-HIGH transition of the clock pulse. The D input must be stable one set-up time prior to the LOW-to-HIGH clock transition for predictable operation.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

#### 2. **Features**

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options
- ESD protection:
  - HBM JESD22-A114E: exceeds 2000 V
  - MM JESD22-A115-A: exceeds 200 V
  - CDM JESD22-C101C: exceeds 1000 V
- Specified from -40 °C to +125 °C

#### **Ordering information** 3.

Table 1. **Ordering information** 

Type number	Package								
	Temperature range	erature range Name Description		Version					
74AHC1G79GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads;	SOT353-1					
74AHCT1G79GW			body width 1.25 mm						
74AHC1G79GV	$-40~^{\circ}\text{C}$ to +125 $^{\circ}\text{C}$	SC-74A	plastic surface-mounted package; 5 leads	SOT753					
74AHCT1G79GV									

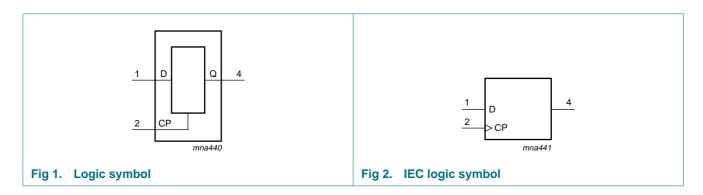


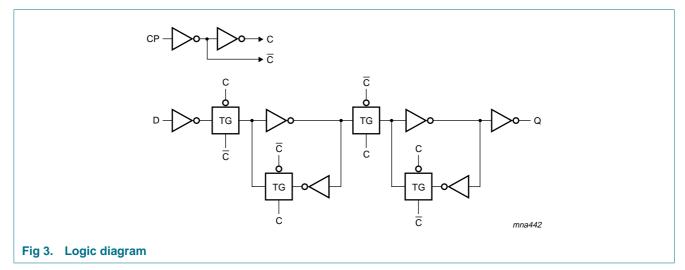
### 4. Marking

Table 2. Marking codes

Type number	Marking
74AHC1G79GW	AP
74AHC1G79GV	A79
74AHCT1G79GW	СР
74AHCT1G79GV	C79

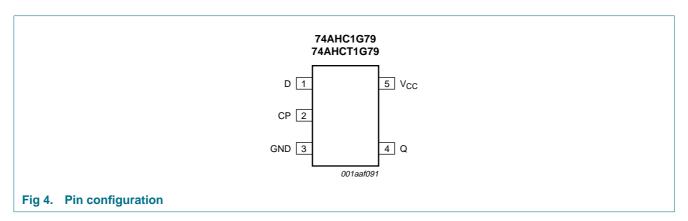
### 5. Functional diagram





### 6. Pinning information

#### 6.1 Pinning



#### 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
D	1	data input
СР	2	clock pulse input
GND	3	ground (0 V)
Q	4	data output
V <sub>CC</sub>	5	supply voltage

### 7. Functional description

Table 4. Function table[1]

Inputs		Output
СР	D	Q + 1
$\uparrow$	L	L
$\uparrow$	Н	Н
L	X	Q

[1] H = HIGH voltage level;

L = LOW voltage level;

↑ = LOW-to-HIGH CP transition;

X = don't care:

Q + 1 = state after the next LOW-to-HIGH CP transition.

### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
$V_{I}$	input voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_{I} < -0.5 \text{ V}$	-20	-	mA
I <sub>OK</sub>	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> _	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I <sub>CC</sub>	supply current		-	75	mA
$I_{GND}$	ground current		-75	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C}$ to +125 $^{\circ}\text{C}$	[2] _	250	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

### 9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74	74AHC1G79			74AHCT1G79		
			Min	Тур	Max	Min	Тур	Max	
$V_{CC}$	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	0	-	5.5	V
Vo	output voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise	$V_{CC}$ = 3.3 V $\pm$ 0.3 V	-	-	100	-	-	-	ns/V
and f	and fall rate	$V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	-	-	20	-	-	20	ns/V

#### 10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
For type	74AHC1G79									
$V_{IH}$	HIGH-level	$V_{CC} = 2.0 \text{ V}$	1.5	-	-	1.5	-	1.5	-	V
	input voltage	V <sub>CC</sub> = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		$V_{CC} = 5.5 \text{ V}$	3.85	-	-	3.85	-	3.85	-	V
$V_{IL}$	LOW-level	$V_{CC} = 2.0 \text{ V}$	-	-	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 3.0 \text{ V}$	-	-	0.9	-	0.9	-	0.9	V
		V <sub>CC</sub> = 5.5 V	-	-	1.65	-	1.65	-	1.65	V

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<sup>[2]</sup> For both TSSOP5 and SC-74A packages: above 87.5 °C the value of Ptot derates linearly with 4.0 mW/K.

**Table 7. Static characteristics** ...continued Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	-40 °C to +125 °C		Uni
			Min	Тур	Max	Min Max	Min	Max		
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$	1						'	
	output voltage	$I_{O} = -50 \mu\text{A};  V_{CC} = 2.0 \text{V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -50 \mu\text{A};  V_{CC} = 3.0 \text{V}$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = -50 \mu A$ ; $V_{CC} = 4.5 \text{ V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.8	-	3.70	-	V
V <sub>OL</sub>	LOW-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_O = 50 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 3.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_O = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
I <sub>I</sub>	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	μΑ
СС	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	40	μΑ
Cı	input capacitance		-	1.5	10	-	10	-	10	pF
For type	74AHCT1G79									
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	-	-	2.0	-	2.0	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	-	-	8.0	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = -50 \mu\text{A}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_0 = -8.0 \text{ mA}$	3.94	-	-	3.8	-	3.70	-	V
V <sub>OL</sub>	LOW-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 8.0 \text{ mA}$	-	-	0.36	-	0.44	-	0.55	V
lı	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μΑ
lcc	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	40	μΑ
ΛI <sub>CC</sub>	additional supply current	per input pin; $V_I = 3.4 \text{ V}$ ; other inputs at $V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 5.5 \text{ V}$	-	-	1.35	-	1.5	-	1.5	m/
Cı	input capacitance		-	1.5	10	-	10	-	10	рF

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### 11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V;  $t_f = t_f = \le 3.0$  ns. For test circuit see Figure 6. For waveforms see Figure 5.

Symbol	Parameter	Conditions			25 °C		-40 °C 1	to +85 °C	-40 °C 1	Unit	
				Min	Тур	Max	Min	Max	Min	Max	
For type	74AHC1G79				'						
t <sub>pd</sub>	propagation	CP to Q	<u>[1]</u>								
	delay	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[2]								
		C <sub>L</sub> = 15 pF		-	4.9	8.4	1.0	9.8	1.0	11.5	ns
		$C_L = 50 pF$		-	6.9	12.0	1.0	14.0	1.0	15.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		$C_{L} = 15 \text{ pF}$		-	3.5	5.6	1.0	7.0	1.0	8.0	ns
		$C_L = 50 pF$		-	5.1	8.0	1.0	10.0	1.0	11.0	ns
t <sub>su</sub>	set-up time	D to CP		3.0	1.0	-	3.0	-	4.0	-	ns
t <sub>h</sub>	hold time	D to CP		+2.0	-1.0	-	2.0	-	3.0	-	ns
t <sub>W</sub>	pulse width	clock HIGH or LOW		3.0	-	-	3.0	-	4.0	-	ns
f <sub>max</sub>	maximum frequency			90	-	-	90	-	70	-	MHz
C <sub>PD</sub>	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}$ ; $f = 1 \text{ MHz}$ ; $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	15	-	-	-	-	-	pF
For type	74AHCT1G7	9									
t <sub>pd</sub>	propagation	CP to Q	<u>[1]</u>								
	delay	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		C <sub>L</sub> = 15 pF		-	3.5	5.0	1.0	6.0	1.0	8.0	ns
		$C_{L} = 50 \text{ pF}$		-	5.0	8.0	1.0	10.0	1.0	11.0	ns
t <sub>su</sub>	set-up time	D to CP		3.0	1.0	-	3.0	-	4.0	-	ns
t <sub>h</sub>	hold time	D to CP		+2.0	-1.0	-	2.0	-	3.0	-	ns
t <sub>W</sub>	pulse width	clock HIGH or LOW		3.0	-	-	3.0	-	4.0	-	ns
f <sub>max</sub>	maximum frequency			90	-	-	90	-	70	-	MHz
C <sub>PD</sub>	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}$ ; $f = 1 \text{ MHz}$ ; $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	16	-	-	-	-	-	pF

<sup>[1]</sup>  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i + \sum{(C_L \times V_{CC}{}^2 \times f_o)}$  where:

f<sub>i</sub> = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in Volts.

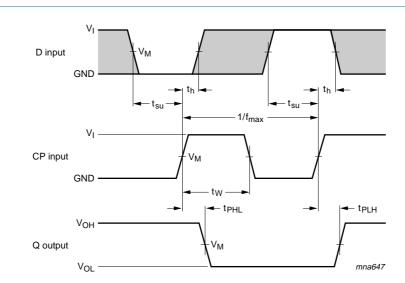
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<sup>[2]</sup> Typical values are measured at  $V_{CC} = 3.3 \text{ V}$ .

<sup>[3]</sup> Typical values are measured at  $V_{CC} = 5.0 \text{ V}$ .

<sup>[4]</sup>  $C_{PD}$  is used to determine the dynamic power dissipation  $P_D$  ( $\mu W$ ).

#### 12. Waveforms



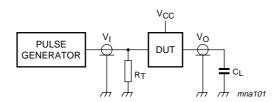
Measurement points are given in Table 9.

V<sub>OL</sub> and V<sub>OH</sub> are typical output voltage levels that occur with the output.

Fig 5. Clock (CP) to output (Q) propagation delay times, clock pulse width, D to set-up times, the CP to D hold times and maximum clock pulse frequency

Table 9. Measurement points

Туре	Inputs	Output	
	VI	V <sub>M</sub>	V <sub>M</sub>
74AHC1G79	GND to V <sub>CC</sub>	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74AHCT1G79	GND to 3.0 V	1.5 V	$0.5 \times V_{CC}$



Test data is given in Table 8. Definitions for test circuit:

 $C_L$  = Load capacitance including jig and probe capacitance.

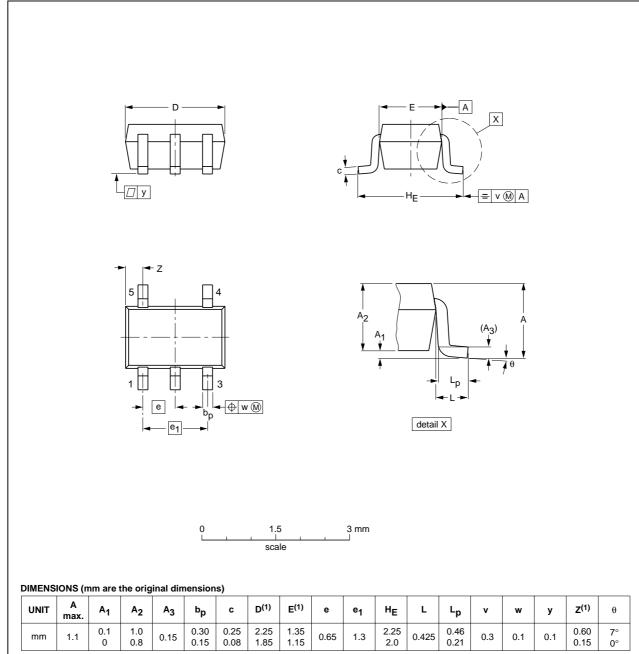
 $R_T$  = Termination resistance should be equal to output impedance  $Z_0$  of the pulse generator.

Fig 6. Load circuitry for switching times

### 13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



#### Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION ISSUE DATE	
SOT353-1		MO-203	SC-88A			<del>-00-09-01</del> 03-02-19

#### Fig 7. Package outline SOT353-1 (TSSOP5)

#### Plastic surface-mounted package; 5 leads

**SOT753** 

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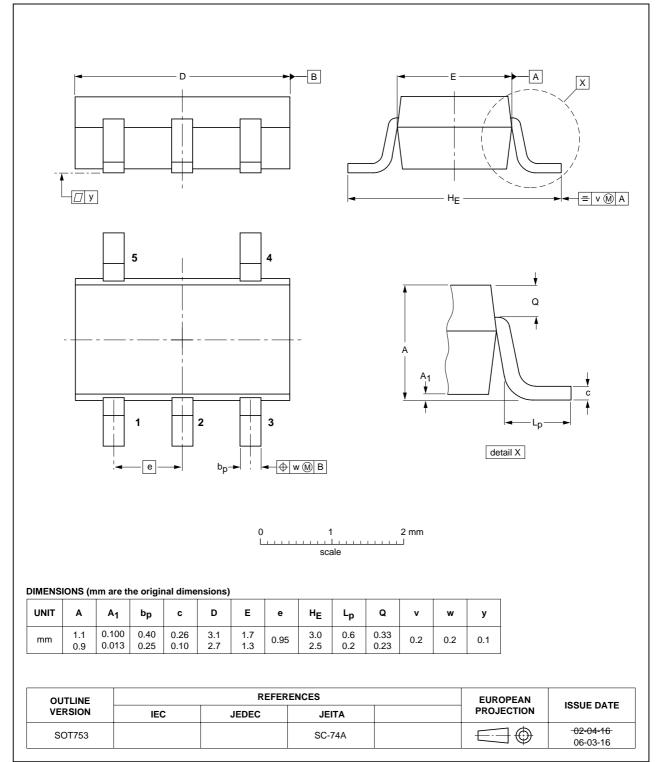


Fig 8. Package outline SOT753 (SC-74A)

**Product data sheet** 

### 14. Abbreviations

#### Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

### 15. Revision history

#### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
74AHC_AHCT1G79_5	20070702	Product data sheet	-	74AHC_AHCT1G79_4		
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>					
	<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>					
	<ul> <li>Package SOT353 changed to SOT353-1 in <u>Section 3</u> and <u>Section 13</u>.</li> </ul>					
	<ul> <li>Figure 5 updated to include waveform definitions for set-up, hold, pulse width and maximum frequency.</li> </ul>					
	<ul> <li>Quick reference data and Soldering sections removed.</li> </ul>					
74AHC_AHCT1G79_4	20020606	Product specification	-	74AHC_AHCT1G79_3		
74AHC_AHCT1G79_3	20020218	Product specification	-	74AHC_AHCT1G79_2		
74AHC_AHCT1G79_2	20010222	Product specification	-	74AHC_AHCT1G79_1		
74AHC_AHCT1G79_1	19990518	Product specification	-	-		

### 74AHC1G79; 74AHCT1G79

Single D-type flip-flop; positive-edge trigger

### 16. Legal information

#### 16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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#### **NXP Semiconductors**

## 74AHC1G79; 74AHCT1G79

Single D-type flip-flop; positive-edge trigger

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